


FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT		ATTY DOCKET NO. 536-009.002		SERIAL NO. 09/319,699	
		APPLICANTS: G. Lippert, et al			
		FILING DATE: July 19, 1999		ART UNIT: 2814	



UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
<i>D. L.</i>	Si Heterojunction Bipolar Transistors, L.D. Lanzerotti; IEDM Technical Digest; International Electronic Devices Meeting; December 11-14, 1994.
	Heterojunction Bipolar Transistors; L.D. Lanzerotti; IEEE; 1996.
	IEDM Technical Digest; International Electronic Devices Meeting; December 8-11, 1996.
	Physics of Semiconductor Devices, 2nd Edition; John Wiley & Sons, Inc., 1981.
	High Speed SiGe-HBT With Very Low Base Sheet Resistivity; E. Kasper; 1993 IEEE.

Examiner <i>Douglas W. [Signature]</i>	Date: <i>3 Feb 04</i>
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<i>Ref</i>		Optimization of SiGe HBT Technology for High Speed Analog and Mixed-Signal Applications; D.L. Hareme; 1993 IEEE.
		2001 IEDM Call for Papers, IEEE International Electron Devices Meeting. (No date provided.)
		2001 IEDM; 2001 IEEE International Electron Devices Meeting; December 3-5, 2001.

Examiner

Wayne Witt

Date:

3 Feb 04